

ABSTRACT**SHORT-CHANNEL TRANSISTORS**

An electronic switching device comprising a source electrode, a drain electrode, an insulating layer in the region between source and drain electrode, a semiconducting layer in contact with both the source and the drain electrode, and in contact with said insulating layer, wherein the smallest distance between said source and drain electrodes is less than 1 μm , and wherein the shape of the insulating layer is such that the path of smallest distance between the source-and drain electrodes intersects through a region of said insulating layer, so as to reduce the OFF current of the electronic switching device.

Figure 1